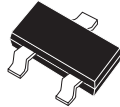


## CMPT2484

**NPN SILICON  
LOW NOISE TRANSISTOR**



**SOT-23 CASE**

### DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT2484 type is an NPN silicon low noise transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for low noise amplifier applications.

**Marking Code is C1U.**

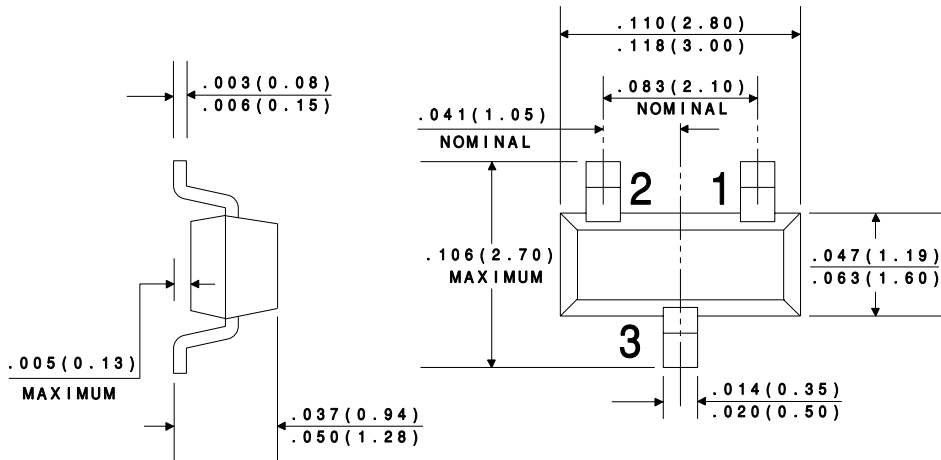
### MAXIMUM RATINGS (T<sub>A</sub>=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V <sub>CB0</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	I <sub>C</sub>	50	mA
Power Dissipation	P <sub>D</sub>	350	mW
Operating and Storage			
Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance	θ <sub>JA</sub>	357	°C/W

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I <sub>CBO</sub>	V <sub>CB</sub> =45V		10	nA
I <sub>CBO</sub>	V <sub>CB</sub> =45V, T <sub>A</sub> =150°C		10	μA
I <sub>EBO</sub>	V <sub>EB</sub> =5.0V		10	nA
BV <sub>CB0</sub>	I <sub>C</sub> =10μA	60		V
BV <sub>CEO</sub>	I <sub>C</sub> =10mA	60		V
BV <sub>EBO</sub>	I <sub>E</sub> =10μA	5.0		V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =1.0mA, I <sub>B</sub> =100μA		0.35	V
V <sub>BE(ON)</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =1.0mA		0.95	V
h <sub>FE</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =1.0mA	250	---	
h <sub>FE</sub>	V <sub>CE</sub> =5.0V, I <sub>C</sub> =10mA	---	800	
C <sub>ob</sub>	V <sub>CB</sub> =5.0V, I <sub>E</sub> =0, f=1.0MHz		6.0	pF
C <sub>ib</sub>	V <sub>EB</sub> =0.5V, I <sub>C</sub> =0, f=1.0MHz		6.0	pF
NF	V <sub>CE</sub> =5.0V, I <sub>C</sub> =10μA, R <sub>S</sub> =10kΩ f=1.0kHz, BW=200Hz		3.0	dB

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR